

High frequency rectifier schottky barrier diode

RB411D

●Applications

Low power rectification
For switching power supply

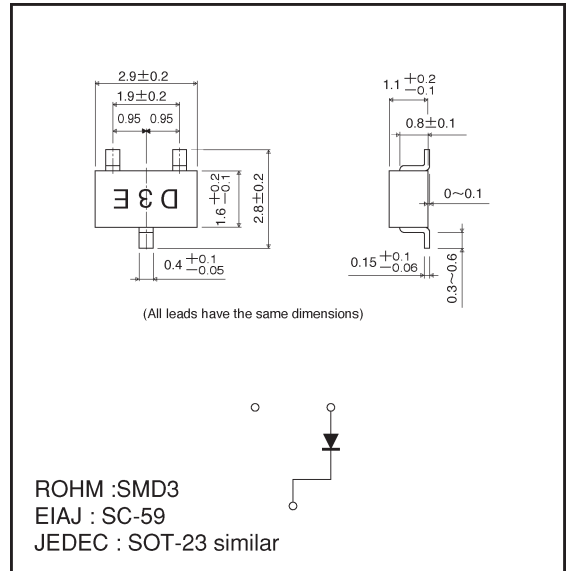
●Features

- 1) Small surface mounting type.(SMD3)
- 2) High reliability.
- 3) Low forward drop voltage.
(typical capability 0.43V at 0.5A)

●Construction

Silicon epitaxial

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	20	V
Mean rectifying current	I_o	0.5	A
Peak forward surge current *	I_{FSM}	3	A
Junction temperature	T_j	125	°C
Storage temperature	T_{slg}	-40~+125	°C

* 60 Hz for 1 μ s

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	—	0.24	0.3	V	$I_F=10\text{mA}$
Forward voltage	V_{F2}	—	0.43	0.5	V	$I_F=500\text{mA}$
Reverse current	I_R	—	5	30	μ A	$V_R=10\text{V}$
Capacitance between terminals	C_T	—	20	—	pF	$V_R=10\text{V}$, $f=1\text{MHz}$

* ESD sensitive product handling required.

● Electrical characteristic curves ($T_a = 25^\circ\text{C}$ unless specified otherwise)

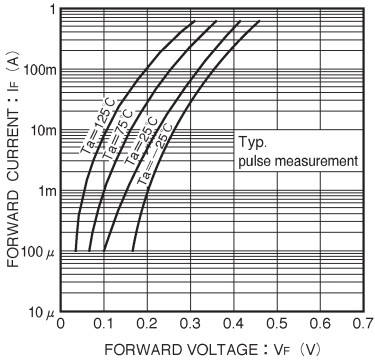


Fig. 1 Forward characteristics

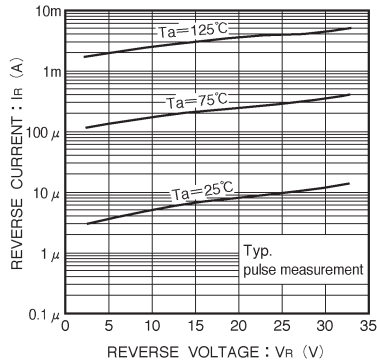


Fig. 2 Reverse characteristics

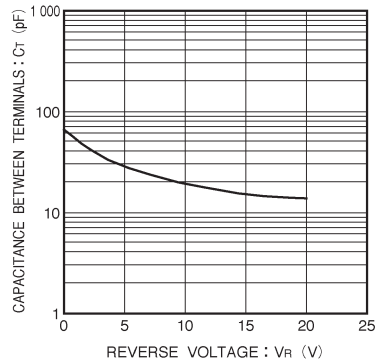


Fig. 3 Capacitance between terminals characteristic